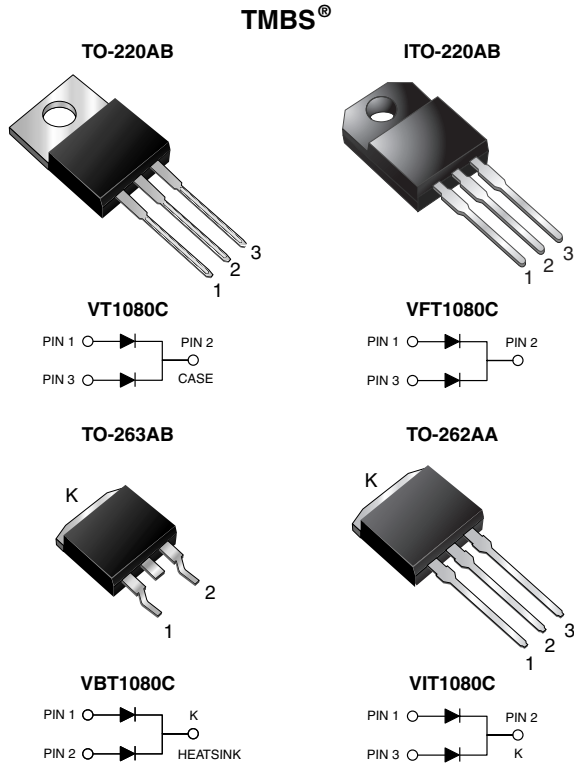


Dual Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.49\text{ V}$ at $I_F = 3\text{ A}$



FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB, ITO-220AB, and TO-262AA package)
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS
COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB and TO-262AA

Molding compound meets UL 94 V-0 flammability rating
Base P/N-E3 - RoHS compliant, commercial grade

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	2 x 5 A
V_{RRM}	80 V
I_{FSM}	80 A
V_F at $I_F = 5\text{ A}$	0.57 V
T_J max.	150 °C

MAXIMUM RATINGS ($T_A = 25\text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	VT1080C	VFT1080C	VBT1080C	VIT1080C	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	80				V
Maximum average forward rectified current (fig. 1)	per device	10				A
	per diode	5				
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	80				A
Non-repetitive avalanche energy at $T_J = 25\text{ °C}$, $L = 60\text{ mH}$ per diode	E_{AS}	30				mJ
Peak repetitive reverse current at $t_p = 2\text{ }\mu\text{s}$, 1 kHz, $T_J = 38\text{ °C} \pm 2\text{ °C}$ per diode	I_{RRM}	1.0				A
Voltage rate of change (rated V_R)	dV/dt	10 000				V/ μs
Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1\text{ min}$	V_{AC}	1500				V
Operating junction and storage temperature range	T_J, T_{STG}	- 55 to + 150				°C

ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Breakdown voltage	I _R = 10 mA	T _A = 25 °C	V _{BR}	80 (minimum)	-	V
Instantaneous forward voltage per diode	I _F = 3 A	T _A = 25 °C	V _F (1)	0.54	-	V
	I _F = 5 A			0.63	0.72	
	I _F = 3 A	T _A = 125 °C		0.49	-	
	I _F = 5 A			0.57	0.66	
Reverse current per diode	V _R = 80 V	T _A = 25 °C	I _R (2)	12	400	μA
		T _A = 125 °C		6	15	mA

Notes

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)							
PARAMETER		SYMBOL	VT1080C	VFT1080C	VBT1080C	VIT1080C	UNIT
Typical thermal resistance	per diode	R _{θJC}	3.5	6.5	3.5	3.5	°C/W
	per device		2.5	5.5	2.5	2.5	

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	VT1080C-E3/4W	1.88	4W	50/tube	Tube
ITO-220AB	VFT1080C-E3/4W	1.70	4W	50/tube	Tube
TO-263AB	VBT1080C-E3/4W	1.35	4W	50/tube	Tube
TO-263AB	VBT1080C-E3/8W	1.35	8W	800/reel	Tape and reel
TO-262AA	VIT1080C-E3/4W	1.43	4W	50/tube	Tube

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

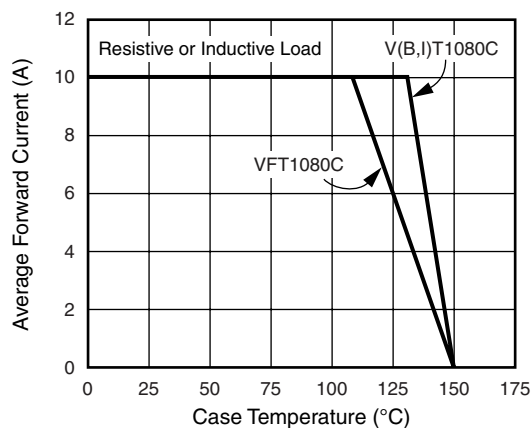


Fig. 1 - Maximum Forward Current Derating Curve

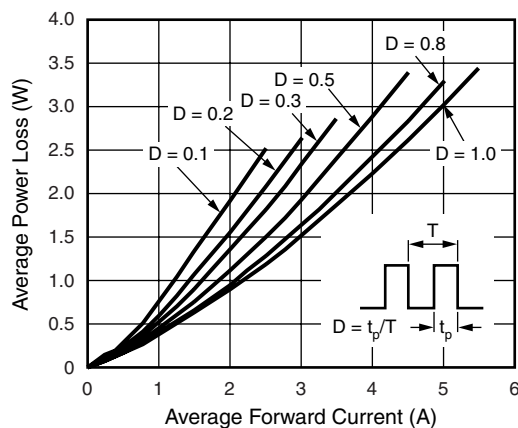


Fig. 2 - Forward Power Loss Characteristics Per Diode

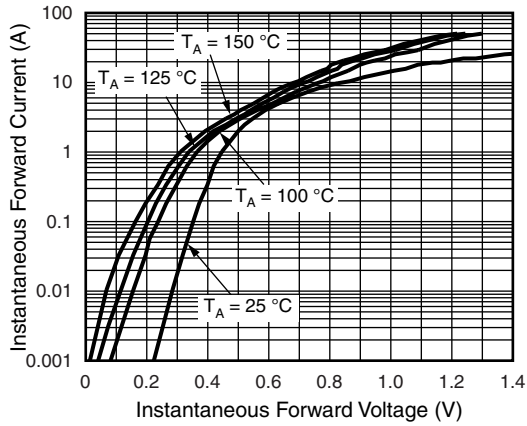


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

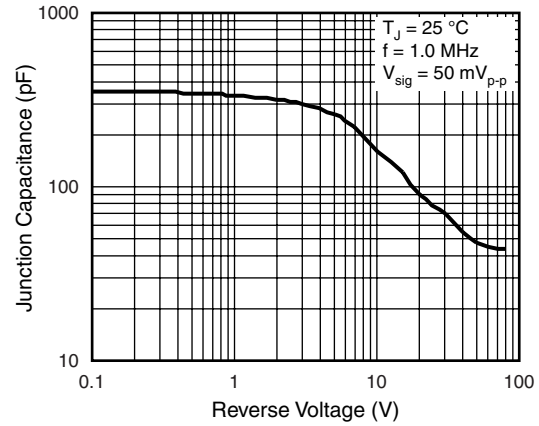


Fig. 5 - Typical Junction Capacitance Per Diode

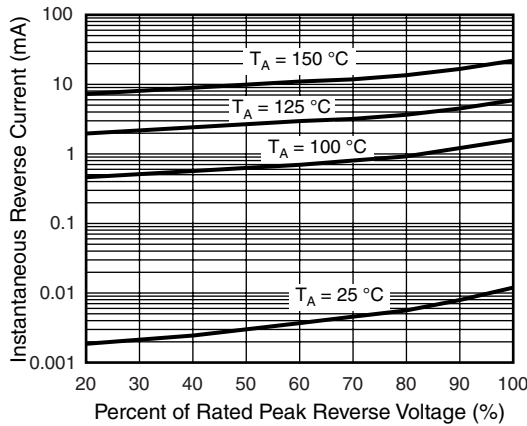


Fig. 4 - Typical Reverse Characteristics Per Diode

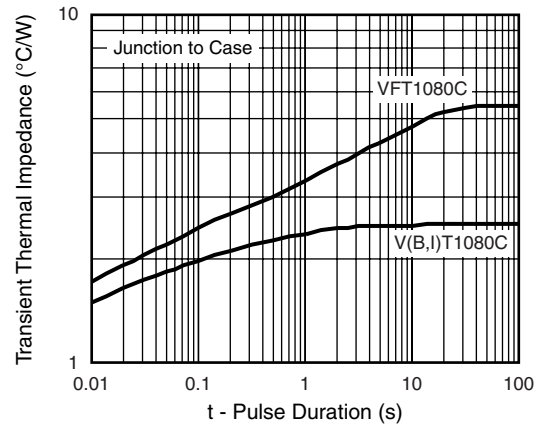


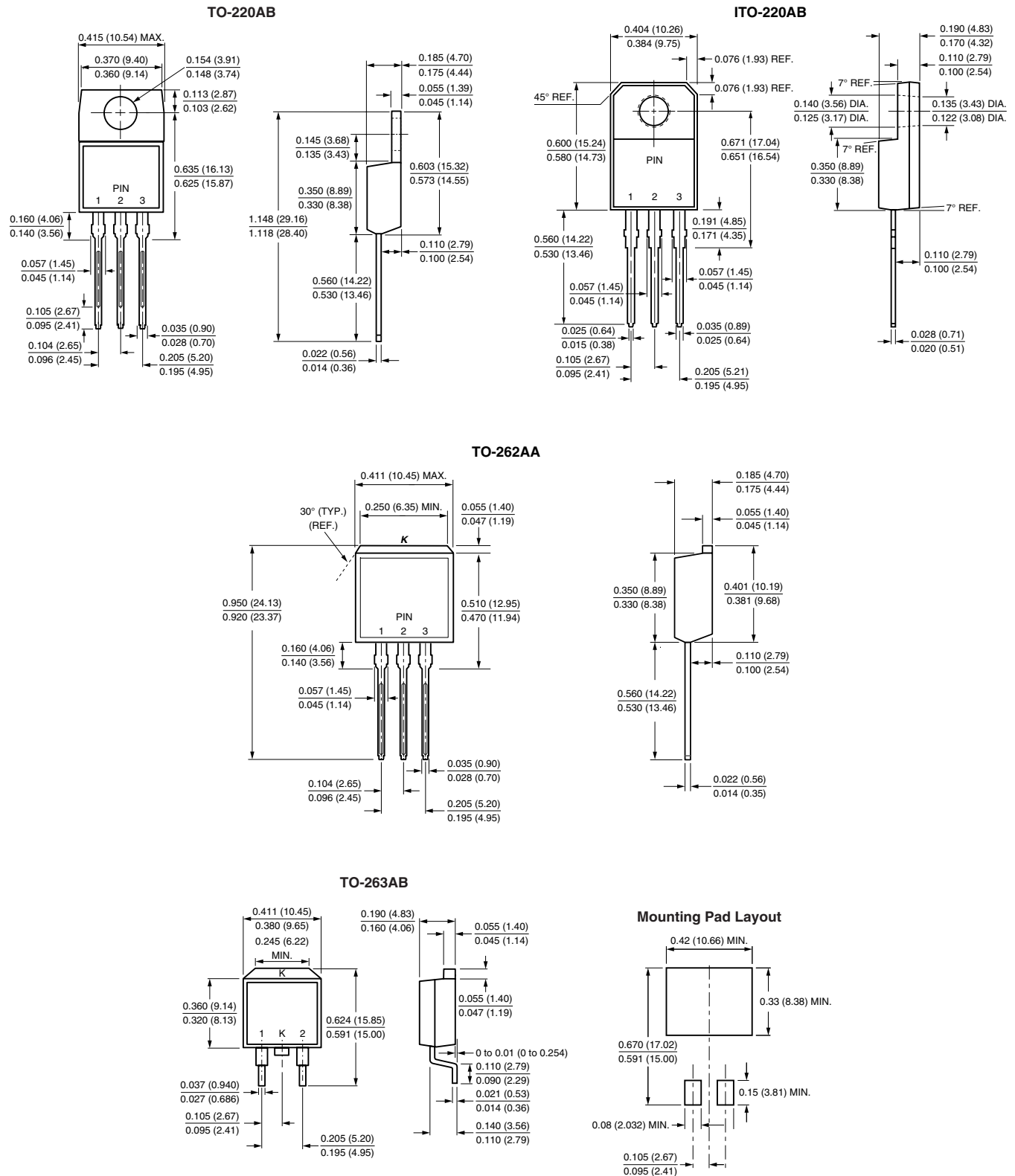
Fig. 6 - Typical Transient Thermal Impedance Per Diode

VT1080C, VFT1080C, VBT1080C, VIT1080C

Vishay General Semiconductor



PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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